

# Artem Baranov

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Low-Temperature Plasma Deposition of III-V Compounds on Silicon for Multijunction Solar Cells. ACS Applied Energy Materials, 2022, 5, 5356-5366.	5.1	0
2	Study of Cryogenic Unmasked Etching of "Black Silicon" with Ar Gas Additives. ACS Omega, 2022, 7, 6053-6057.	3.5	3
3	Lanthanide(III)-Incorporating Polysiloxanes as Materials for Light-Emitting Devices. ACS Applied Polymer Materials, 2022, 4, 2683-2690.	4.4	11
4	Effect of Cryogenic Dry Etching on Minority Charge Carrier Lifetime in Silicon. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900534.	1.8	3
5	The Study of Latex Sphere Lithography for High Aspect Ratio Dry Silicon Etching. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900535.	1.8	13
6	GaNp-based photovoltaic device integrated on Si substrate. Solar Energy Materials and Solar Cells, 2020, 206, 110282.	6.2	11
7	Study of GaP Nucleation Layers Grown on Si by Plasma-Enhanced Atomic Layer Deposition. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900532.	1.8	1
8	Defect properties of solar cells with layers of GaP based dilute nitrides grown by molecular beam epitaxy. Journal of Applied Physics, 2020, 128, 023105.	2.5	4
9	GaPAsN-based light-emitting diode on silicon. Optics and Laser Technology, 2020, 129, 106308.	4.6	2
10	Interface Properties of GaP/Si Heterojunction Fabricated by PE-ALD. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800617.	1.8	8
11	Low temperature plasma enhanced deposition approach for fabrication of microcrystalline GaP/Si superlattice. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, 02D408.	2.1	7
12	Defect properties of InGaAsN layers grown as sub-monolayer digital alloys by molecular beam epitaxy. Journal of Applied Physics, 2018, 123, .	2.5	8
13	Precision Chemical Etching of GaP(NAs) Epitaxial Layers for the Formation of Monolithic Optoelectronic Devices. Semiconductors, 2018, 52, 1775-1781.	0.5	1
14	Influence of PE-ALD of GaP on the Silicon Wafers Quality. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700685.	1.8	2
15	Study of GaP/Si Heterojunction Solar Cells. Energy Procedia, 2016, 102, 56-63.	1.8	22
16	Admittance spectroscopy of solar cells based on GaPNAs layers. Semiconductors, 2015, 49, 524-528.	0.5	2
17	Impact of interface recombination on quantum efficiency of Si:H/c-Si solar cells based on Si wires. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100339.	1.8	4